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6500 MICROPROCESSORS

THE 6500 MICROPROCESSOR FAMILY CONCEPT -----

The 6500 Series Microprocessors represent the first totally software compatible microprocessor family. This family of products includes a range of software compatible microprocessors which provide a selection of addressable memory range, interrupt input options and on-chip clock oscillators and drivers. All of the microprocessors in the 6500 group are software compatible within the group and are bus compatible with the M6800 product offering.

The family includes six microprocessors with on-board clock oscillators and drivers and four microprocessors driven by external clocks. The on-chip clock versions are aimed at high performance, low cost applications where single phase inputs, crystal or RC inputs provide the time base. The external clock versions are geared for the multi processor system applications where maximum timing control is mandatory. All versions of the microprocessors are available in 1 MHz, 2 MHz ("A" suffix on product numbers), and 3 MHz ("B" suffix on product numbers) maximum operating frequencies.

FEATURES OF THE 6500 FAMILY

- Single + 5 volt supply
- N channel, silicon gate, depletion load technology
- · Eight bit parallel processing
- 56 Instructions
- Decimal and binary arithmetic
- Thirteen addressing modes
- True indexing capability
- Programmable stack pointer
- Variable length stack
- Interrupt capability
- Non-maskable interrupt
- Use with any type or speed memory

- 8 BIT Bi-directional Data Bus
- Addressable memory range of up to 65K bytes
- "Ready" input (for single cycle execution)
- Direct memory access capability
- Bus compatible with M6800
- Choice of external or on-board clocks
- 1 MHz, 2 MHz, and 3 MHz operation
- On-the-chip clock options
 - * External single clock input
 - * RC time base input
 - * Crystal time base input
- Pipeline architecture

MEMBERS OF THE 6500 MICROPROCESSOR (CPU) FAMILY		ORDER NUMBER: MXS 65XX
Microprocessors	with On-Chip Clock Oscillator	
Model	Addressable Memory	
R6502	65K Bytes	
R6503	4K Bytes	
R6504	8K Bytes	
R6505	4K Bytes	FREQUENCY RANGE
R6506	4K Bytes	NO SUFFIX = 1 MHz
R6507	8K Bytes	A = 2 MHz
Microprocessors	with External Two Phase	B = 3 MHz
Clock Inputs		MODEL DESIGNATOR
Model	Addressable Memory	XX = 02, 03, 04, 15
R6512	65K Bytes	
R6513	4K Bytes	PACKAGE DESIGNATOR
R6514	8K Bytes	C = CERAMIC
R6515	4K Bytes	P = PLASTIC

COMMENTS ON THE DATA SHEET

The data sheet is constructed to review first the basic "Common Characteristics"—those features which are common to the general family of microprocessors. Subsequent to a review of the family characteristics will be sections devoted to each member of the group with specific features of each.



Note: 1. Clock Generator is not included on 6512,13,14,15 2. Addressing Capability and control options vary with each of the 6500 Products.

6500 Internal Architecture

MAXIMUM RATINGS

RATING	SYMBOL	VALUE	UNIT
SUPPLY VOLTAGE	Vcc	-0.3 to +7.0	Vdc
INPUT VOLTAGE	Vin	-0.3 to +7.0	Vdc
OPERATING TEMPERATURE	TA	0 to +70	°C
STORAGE TEMPERATURE	TSTG	- 55 to + 150	°C

This device contains input protection against damage due to high static voltages or electric fields; however, precautions should be taken to avoid application of voltages higher than the maximum rating.

ELECTRICAL CHARACTERISTICS (Vcc = 5.0V ± 5%, Vss = 0, T_A = 0° to + 70°C) $\varnothing_1, \varnothing_2$ (in) applies to 6512, 13, 14, 15; $\Im \circ$ (in) applies to 6502, 03, 04, 05, 06 and 07

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT
Input High Voltage					
Logic,∅∘ (in)		Vss + 2.4	-	Vcc	Vdc
Ø ₁ ,Ø ₂ (in)	VIH	Vcc - 0.2	-	Vcc + 1.0V	Vdc
Input High Voltage					
RES, NMI, RDY, IRQ, Data, S.O.		Vss + 2.0	_	—	Vdc
Input Low Voltage					
Logic,⊘ _{° (in)}		Vss – 0.3	-	Vss + 0.4	Vdc
Ø,,Ø ₂ (in)	VIL	Vss - 0.3	-	Vss + 0.2	Vdc
RES, NMI, RDY, IRQ, Data, S.O.		-	_	Vss + 0.8	Vdc
Input Leakage Current					
$(V_{in} = 0 \text{ to } 5.25V, Vcc = 5.25V)$					
Logic (Excl. RDY,S.O.)	lin	-	-	2.5	μA
$\emptyset_1, \emptyset_2(in)$		-	-	100	μA
ذ(in)		-	-	10.0	μA
Three State (Off State) Input Current					- N.
$(V_{in} = 0.4 \text{ to } 2.4V, Vcc = 5.25V)$					
Data Lines	ITSI	-	-	10	μA
Output High Voltage					
$(I_{OH} = -100\mu Adc, Vcc = 4.75V)$					
SYNC, Data, AO-A15, R/W	VOH	Vss + 2.4	-	-	Vdc
Out Low Voltage					
$(I_{OL} = 1.6 \text{mAdc}, \text{Vcc} = 4.75 \text{V})$					
SYNC, Data, AO-A15, R/W	VOL	—	_	Vss + 0.4	Vdc
Power Dissipation	PD	_	.35	.80	w
Capacitance	с				pF
$(V_{in} = 0, T_A = 25^{\circ}C, f = 1MHz)$					
Logic	C _{in}	-	-	10	
Data		_	_	15	
AO-A15,RW, SYNC	Cout	-		12	
ذ(in)	C _{ذ(in)}	-	-	15	
Ø	C _Ø ,	-	30	50	
Ø	C⊘	_	50	80	

Note: IRQ and NMI require 3K pull-up resistors.



Clock Timing-MCS6512, 13, 14, 15



Timing for Writing Data to Memory or Peripherals



Timing for Writing Data to Memory or Peripherals

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TMDS

1 MH_z TIMING

2 MH_z TIMING

3 MH_z TIMING

Electrical Characteristics: (Vcc = 5V \pm 5%, Vss = 0 V, T_A = 0°-70°C)

CLOCK TIMING-6502, 03, 04, 05, 06, 07

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.
Cycle Time	тсус	1000	-	-
Ø _{0(IN)} Pulse Width (measured at 1.5v)	PWHØ0	460	-	520
Ø _{0 (IN)} Rise, Fall Time	TRØ ₀ ,TFØ ₀	_	-	10
Delay Time between Clocks (measured at 1.5v)	т _D	5	-	-
Ø 1(OUT) Pulse Width (measured at 1.5v)	PWHØ1	PWHØOL-20	-	PWHØOL
2(OUT) Pulse Width (measured at 1.5v)	PWHØ2	PWHØOH-40	-	PWHØ _{OH} - 10
⁽²⁾ 1(OUT) ^{, (2)} 2(OUT) Rise, Fall Time (measured .8v to 2.0v) (Load ½ 30pf ½ 1 TTL)	T _R , T _F	-	-	25

MIN.	TYP.	MAX.
500	-	-
240		260
-	-	10
5	-	_
PWHØ _{OL} -20	-	PWHØOL
PWHØOH-40	1 <u>8-</u>	PWHØOH-10
-	-	25

TYP.	MAX.	UNITS
-	-	ns
-	170	ns
-	10	ns
-	-	ns
-	PWHØOL	ns
-	PWHØOH-10	ns
-	25	ns
	TYP. 	 − 170 − 10 − − − PWHØ_{OL} −

CLOCK TIMING-6512, 13, 14, 15

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.
Cycle Time	Тсус	1000	-	-
Clock Pulse Width Ø1	PWH Ø1	430		
(Measured at V _{CC} - 0.2v) Ø2	PWH Ø2	470	-	-
Fall Time, Rise Time	1			
(Measured from 0.2v to $V_{CC} - 0.2v$)	T _F ,T _R	-	-	25
Delay Time between Clocks				
(Measured at 0.2v)	Тр	0	-	-

MIN.	TYP.	MAX.
500	-	_
215		
235	-	-
_	_	15
0	_	ر المر 1999 – ماريد

MIN.	TYP.	MAX.	UNITS
333	-	-	ns
150			ns
160	-	-	
			÷
	-	15	ns
	1		
0	-	-	ns

READ/WRITE TIMING (LOAD = ITTL)

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	MIN.	TY
Read/Write Setup Time from 6500	TRWS	-	100	300	-	10
Address Setup Time from 6500	TADS	-	100	300	-	10
Memory Read Access Time	TACC	-	-	575	-	-
Data Stability Time Period	TDSU	100	-	-	50	-
Data Hold Time-Read	THR	10	-	-	10	-
Data Hold Time-Write	THW	30	60	-	30	6
Data Setup Time from 6500	TMDS	-	150	200	-	7
S.O. Setup Time	T _{S.O.}	100	-	<u></u>	50	-
SYNC Setup Time from 6500	TSYNC	-	-	350	-	-
Address Hold Time	THA	30	60	-	30	6
R/W Hold Time	THRW	30	60	-	30	6
RDY Setup Time	TRDY	100	-	-	50	-

MIN.	TYP.	MAX.
-	100	150
_	100	150
_	+	300
50	-	-
10	-	-
30	60	-
_	75	100
50	-	-
_	-	175
30	60	-
30	60	-
50	-	-

MIN.	TYP.	MAX.	UNITS
-	80	110	ns
-	80	125	ns
-	-	170	ns
50	-	-	ns
10	-	-	ns
10	-	-	ns
_	70	100	ns
50	-	-	ns
	-	120	ns
10	30	-	ns
10	30	-	ns
-	-	15	ns

6500 SIGNAL DESCRIPTION

Clocks (\emptyset_1, \emptyset_2)

The 651X requires a two phase non-overlapping clock that runs at the Vcc voltage level. The 650X clocks are supplied with an internal clock generator. The frequency of these clocks is externally controlled.

Address Bus (A₀-A₁₅)

These outputs are TTL compatible, capable of driving one standard TTL load and 130 pf.

Data Bus (D₀-D₇)

Eight pins are used for the data bus. This is a bi-directional bus, transferring data to and from the device and peripherals. The outputs are tri-state buffers capable of driving one standard TTL load and 130pf.

Data Bus Enable (DBE)

This TTL compatible input allows external control of the tri-state data output buffers and will enable the microprocessor bus driver when in the high state. In normal operation DBE would be driven by the phase two (\emptyset_2) clock, thus allowing data output from microprocessor only during \emptyset_2 . During the read cycle, the data bus drivers are internally disabled, becoming essentially an open circuit. To disable data bus drivers externally, DBE should be held low.

Ready (RDY)

This input signal allows the user to single cycle the microprocessor on all cycles except write cycles. A negative transition to the low state during or coincident with phase one (\emptyset_1) and up to 100ns after phase two (\emptyset_2) will halt the microprocessor with the output address lines reflecting the current address being fetched. This condition will remain through a subsequent phase two (\emptyset_2) in which the Ready signal is low. This feature allows microprocessor interfacing with low speed PROMS as well as fast (max. 2 cycle) Direct Memory Access (DMA). If Ready is low during a write cycle, it is ignored until the following read operation.

Interrupt Request (IRQ)

This TTL level input requests that an interrupt sequence begin within the microprocessor. The microprocessor will complete the current instruction being executed before recognizing the request. At that time, the interrupt mask bit in the Status Code Register will be examined. If the interrupt mask flag is not set, the microprocessor will begin an interrupt sequence. The Program Counter and Processor Status Register are stored in the stack. The microprocessor will then set the interrupt mask flag high so that no further interrupts may occur. At the end of this cycle, the program counter low will be loaded from address FFFE, and program counter high from location FFFF, therefore transferring program control to the memory vector located at these addresses. The RDY signal must be in the high state for any interrupt to be recognized. A 3KΩ external resistor should be used for proper wire-OR operation.

Non-Maskable Interrupt (NMI)

A negative going edge on this input requests that a non-maskable interrupt sequence be generated within the microprocessor. NMI is an unconditional interrupt. Following completion of the current instruction, the sequence of operations defined for IRQ will be performed, regardless of the interrupt mask flag status. The vector address loaded into the program counter, low and high, are locations FFFA and FFFB respectively, thereby transferring program control to the memory vector located at these addresses. The instructions loaded at these locations cause the microprocessor to branch to a non-maskable interrupt routine in memory.

NMI also requires an external 3KΩ resister to Vcc for proper wire-OR operations.

Inputs IRQ and NMI are hardware interrupt lines that are sampled during \emptyset_2 (phase 2) and will begin the appropriate interrupt routine on the \emptyset_1 (phase 1) following the completion of the current instruction.

Set Overflow Flag (S.O.)

A NEGATIVE going edge on this input sets the overflow bit in the Status Code Register. This signal is sampled on the trailing edge of \emptyset_1 .

SYNC

This output line is provided to identify those cycles in which the microprocessor is doing an OP CODE fetch. The SYNC line goes high during \emptyset_1 of an OP CODE fetch and stays high for the remainder of that cycle. If the RDY line is pulled low during the \emptyset_1 clock pulse in which SYNC went high, the processor will stop in its current state and will remain in the state until the RDY line goes high. In this manner, the SYNC signal can be used to control RDY to cause single instruction execution.

Reset

This input is used to reset or start the microprocessor from a power down condition. During the time that this line is held low, writing to or from the microprocessor is inhibited. When a positive edge is detected on the input, the microprocessor will immediately begin the reset sequence.

After a system initialization time of six clock cycles, the mask interrupt flag will be set and the microprocessor will load the program counter from the memory vector locations FFFC and FFFD. This is the start location for program control.

After Vcc reaches 4.75 volts in a power up routine, reset must be held low for at least two clock cycles. At this time the R/W and (SYNC) signal will become valid.

When the reset signal goes high following these two clock cycles, the microprocessor will proceed with the normal reset procedure detailed above.

ADDRESSING MODES

ACCUMULATOR ADDRESSING—This form of addressing is represented with a one byte instruction, implying an operation on the accumulator.

IMMEDIATE ADDRESSING—In immediate addressing, the operand is contained in the second byte of the instruction, with no further memory addressing required.

ABSOLUTE ADDRESSING—In absolute addressing, the second byte of the instruction specifies the eight low order bits of the effective address while the third byte specifies the eight high order bits. Thus, the absolute addressing mode allows access to the entire 65K bytes of addressable memory.

ZERO PAGE ADDRESSING—The zero page instructions allow for shorter code and execution times by only fetching the second byte of the instruction and assuming a zero high address byte. Careful use of the zero page can result in significant increase in code efficiency.

INDEXED ZERO PAGE ADDRESSING—(X, Y indexing)—This form of addressing is used in conjunction with the index register and is referred to as "Zero Page, X" or "Zero Page, Y." The effective address is calculated by adding the second byte to the contents of the index register. Since this is a form of "Zero Page" addressing, the content of the second byte references a location in page zero. Additionally, due to the "Zero Page" addressing nature of this mode, no carry is added to the high order 8 bits of memory and crossing of page boundaries does not occur.

INDEXED ABSOLUTE ADDRESSING—(X, Y indexing)—This form of addressing is used in conjunction with X and Y index register and is referred to as "Absolute, X," and "Absolute, Y." The effective address is formed by adding the contents of X and Y to the address contained in the second and third bytes of the instruction. This mode allows the index register to contain the index or count value and the instruction to contain the base address. This type of indexing allows any location referencing and the index to modify multiple fields resulting in reduced coding and execution time.

IMPLIED ADDRESSING—In the implied addressing mode, the address containing the operand is implicitly stated in the operation code of the instruction.

RELATIVE ADDRESSING—Relative addressing is used only with branch instructions and establishes a destination for the conditional branch.

The second byte of the instruction becomes the operand which is an "Offset" added to the contents of the lower eight bits of the program counter when the counter is set at the next instruction. The range of the offset is -128 to + 127 bytes from the next instruction.

INDEXED INDIRECT ADDRESSING—In indexed indirect addressing (referred to as (Indirect, X)), the second byte of the instruction is added to the contents of the X index register, discarding the carry. The result of this addition points to a memory location on page zero whose contents is the low order eight bits of the effective address. The next memory location in page zero contains the high order eight bits of the effective address. Both memory locations specifying the high and low order bytes of the effective address must be in page zero.

INDIRECT INDEXED ADDRESSING—In indirect indexed addressing (referred to as (Indirect), Y), the second byte of the instruction points to a memory location in page zero. The contents of this memory location is added to the contents of the Y index register, the result being the low order eight bits of the effective address. The carry from this addition is added to the contents of the next page zero memory location, the result being the high order eight bits of the effective address.

ABSOLUTE INDIRECT—The second byte of the instruction contains the low order eight bits of a memory location. The high order eight bits of that memory location is contained in the third byte of the instruction. The contents of the fully specified memory location is the low order byte of the effective address. The next memory location contains the high order byte of the effective address which is loaded into the sixteen bits of the program counter.

INSTRUCTION SET—ALPHABETIC SEQUENCE

ADC	Add Memory to Accumulator with Carry	LDA	Load Accumulator with Memory
AND	"AND" Memory with Accumulator	LDX	Load Index X with Memory
ASL	Shift left One Bit (Memory or Accumulator)	LDY	Load Index Y with Memory
BCC	Branch on Carry Clear	LSR	Shift One Bit Right (Memory or Accumulator)
BCS BEQ	Branch on Carry Set Branch on Result Zero	NOP	No Operation
BIT	Test Bits in Memory with Accumulator	ORA	"OR" Memory with Accumulator
BMI BNE BPL BRK BVC	Branch on Result Minus Branch on Result not Zero Branch on Result Plus Force Break Branch on Overflow Clear	PHA PHP PLA PLP	Push Accumulator on Stack Push Processor Status on Stack Pull Accumulator from Stack Pull Processor Status from Stack
BVS	Branch on Overflow Set	ROL	Rotate One Bit Left (Memory or Accumulator)
CLC	Clear Carry Flag	ROR	Rotate One Bit Right (Memory or Accumulator)
CLD	Clear Decimal Mode	RTI	Return from Interrupt
CLI	Clear Interrupt Disable Bit	RTS	Return from Subroutine
CLV	Clear Overflow Flag	SBC	Subtract Memory from Accumulator with Borrow
CMP	Compare Memory and Accumulator	SEC	Set Carry Flag
CPX	Compare Memory and Index X	SED	Set Decimal Mode
CPY	Compare Memory and Index Y	SEI	Set Interrupt Disable Status
DEC	Decrement Memory by One	STA	Store Accumulator in Memory
DEX	Decrement Index X by One	STX	Store Index X in Memory
DEY	Decrement Index Y by One	STY	Store Index Y in Memory
EOR	"Exclusive-or" Memory with Accumulator	TAX	Transfer Accumulator to Index X
INC	Increment Memory by One	TAY	Transfer Accumulator to Index Y
INX	Increment Index X by One	TSX	Transfer Stack Pointer to Index X
INY	Increment Index Y by One	TXA	Transfer Index X to Accumulator
JMP	Jump to New Location	TXS	Transfer Index X to Stack Register
JSR	Jump to New Location Saving Return Address	TYA	Transfer Index Y to Accumulator



INSTRUCTION SET – OP CODES, Execution Time, Memory Requirements

		-	-		-	-		-	-				Т				-			-	•		-	ī	-		Т	-		-			-		ī		-	•						
	671 6A1100	0	N	1-	0	N	-	0	N	•	0	N	• •	PN		0	N		0	N	-	0	N			1	.0			0	N	•	0	N	-	•	N	•	N	z	с	1	D	2
ADC	A+M+C-A (4)(1)	69	2	2	60	4	3	65	3	2			Т	Т	Т	61	6	2	71	5	2	75	4	2 7	0	1	7	9 4	3						Т			П	1	1	1	-	-	7
AND	AAM-A (1)	25	2	2	2	•	3	25	3	2						21	6	2	31	5	2	35	4	2 3	0		3	9 4	3												-	-	-	-
ASL	C < 7 0 < 0					6	3	66	5	2		2										16	6	2 1	E	1 3																-	-	-
acc	BRANCH ON C-8 (2)												L																	90	2	2							-	-	-	-	-	-
ecs.	BRANCH ON C+1 (2)																														2	2							-	-	-	-	-	-
BEQ	BRANCH ON Z+1 (2)		T	Г		T							T		T									T			Т	T	T	FO	2	2			Т			П	-	-	-	-	-	-
817	AAM				20	4	3	24	3	2																	1												м,	1	-		- 1	4
BMI	BRANCH ON N+1 (2)																										L.			30	2	2							-	-	-	-	-	-
BNE	BRANCH ON 2-8 (2)																													De	2	2							-	-	-	-	-	- 1
BPL	BRANCH ON N-8 (2)																													10	2	2							-	-	-	-	-	-
BRK	(See Fig. 1)	Г	Т	Г		Т							•	7	1									Т	T	Т	Г	Т	Т						Т				-	-	-	-	-	7
BVC	BRANCH ON V-8 (2)			E																										50	2	2							-	-	-	-	-	-
BVS	BRANCH ON V-1 (2)																													70	2	2							-	-	-	-		-
CLC	0 - C												l.	8 2	1																								-	-	•	-		-
CLD	• - D													8 2																			-						-	-	-	-	•	-
CLI	0 = 1		Т	Г		Т							5	8 2	1									Т		Т	Г	Т											-	-	-	•		-
CLV	• - v													8 2	1																								-	-	-	-	- (•
CMP	A-M (1)	C	9 2	2	C	•	3	CS	3	2						C	6	2	DI	5	2	D5	4	2 0	00	1	0	9 4	3												1	-		- 1
CPX	х-м		- 1 -	1.	1.1.1			E4	1.1	-																													1	1				-
CPY	Y-M	C	2	2				C4																				1			Ц				_				1	1	1	-		-
DEC	M-1 - M				C	6	3	C6	5	2												D6	6	2 0	DE	1													1	1				-
DEX	X-1 - X													A 2													L												1	1				-
DEY	$Y - 1 \rightarrow Y$												8	8 2	1												L												1	1				-
EOR	A - M - A (1)	49	2	2				45								41	6	2	51	5					D			9 4	3										1	1				-
INC	M + 1 - M		+	1	E	6	3	E6	5	2			+	+	1							F6	6	2 F	E	1		+	1		\square	-	_	4	4	_	$ \rightarrow $	4	1.	1	-	-		-
INX	X + 1 - X													8 2																									1	1	-	-		-
INY	V + 1 - Y												C	8 2	1																		1						1	1	-	-		-1
JMP	JUMP TO NEW LOC					3																											6C	5	3				-	-	-	-		-
JSR	(See Fig. 2) JUMP SUB					6																																	-	-	-	-		-
LDA	M - A (1)	1	9 2	2	~	•	3	A5	3	2						A1	6	2	81	5	2	85	4	2 8	30	13		9 4	3										1	1	-	-	-	-



Note: MOS Technology cannot assume liability for the use of undefined OP Codes

vss -1		6502—40 Pin Package
RDY 2 \$ 1 (OUT) 3	39 \$\$ \$\$ \$0.	
	37 0 \$ 0 (IN)	Features of 6502
N.C. 5	36 N.C.	 65K Addressable Bytes of Memory (A0-A15)
	35 N.C. 34 R/W	IRQ Interrupt
VCC de	33 00	On-the-chip Clock
A0 C 9	32 0 1	TTL Level Single Phase Input
A1 10 A2 11	31 D2 30 D 03	RC Time Base Input
A3 C12	29 04	Crystal Time Base Input
A4 C 13	28 05	 SYNC Signal (can be used for single instruction execution)
A5 14 A6 15	27 D6 26 D7	RDY Signal
A7 16	25 A15	(can be used to halt or single cycle execution)
A8 C 17	24 14	Two Phase Output Clock for Timing of
A9 18 A10 19	23 A13 22 A12	Support Chips
A11 20	21 VSS	NMI Interrupt
	28 \$\$ \$\$ \$\$ \$\$ \$\$ \$\$ \$\$ \$\$ \$\$ \$\$ \$\$ \$\$ \$\$	
	27 0 00 (IN)	
IRQ C3	26 3 R/W	6503—28 Pin Package
	25 D0 24 D1	
A0 06	23 02	Features of 6503
A1 7	22 03	 4K Addressable Bytes of Memory (A0-A11)
A2 68 A3 9	21 D4 20 D5	On-the-chip Clock
A4 10	19 06	IRQ Interrupt
A5 C 11	18 07	NMI Interrupt
A6 12 A7 13	17 A11 16 A10	 8 Bit Bidirectional Data Bus
A7 13 A8 14	15 A9	
RES C1	28 - \$2 (OUT)	
VSS C 2	27 0 0 (IN)	
IRQ 3	26 R/W	6504—28 Pin Package
	25 D0 24 D1	
A1 C6	23 02	Features of 6504
A2 7	22 03	 8K Addressable Bytes of Memory (A0-A12)
A3 8 A4 9	21 D4 20 D5	On-the-chip Clock
A5 C 10	19 06	IRQ Interrupt
A6 [11 A7 [12	18 07 17 A12	 8 Bit Bidirectional Data Bus
A8 C 13	16 A11	
A9 14	15 A10	
RES C	28 0UT)	
VSS C 2	27 0 0 (IN)	6505—28 Pin Package
	26 A/W 25 D 00	0505-20 Fill Fackage
VCC 5	24 01	Features of 6505
A0 G 6	23 02	
A1 7 A2 8	22 D 03 21 D 04	4K Addressable Bytes of Memory (A0-A11)
A3 C9	20 05	 On-the-chip Clock IRQ Interrupt
A4 C 10	19 06	RO Interrupt RDY Signal
A5 11 A6 12	18 D7 17 A11	8 Bit Bidirectional Data Bus
A6 12 A7 13	16 410	- o bit bidirottorial bata bus
A8 C14	15 A9	

RES		1	28	\$ \$ \$ 10UT
VSS		2	27	$\Box \phi_0 (IN)$
Ø1.10UT)	3	26	R/W
IRO		4	25	D D0
VCC		5	24	D D1
A0			23	D2
A1		7	22	03
A2			21	D4
A3		9	20	D5
A4		10	19	De
A5		11	18	70
A6		12	17	A11
A7		13	16	A10
A8		14	15	A9

6506-28 Pin Package

Features of 6506

- 4K Addressable Bytes of Memory (A0-A11)
- On-the-chip Clock
- **IRQ** Interrupt
- Two phase output clock for timing of support chips
- 8 Bit Bidirectional Data Bus

RES C	1	28	φ ₂ (ουτ)
		27	φ ₀ (IN)
RDYC	3	26	R/W
vcc 🗖	4	25	
A0 🗖	5	24	10
A1 🗖	6	23	D2
A2 🗖	7	22	03
A3 🗖	8	21	D4
A4 🗖	9	20	D5
A5 🗖	10	19	D6
A6 🗖	11	18	70
A7 C	12	17	A12
A8 🗖	13	16	A11
A9 🗖	14	15	A10

6507-28 Pin Package

Features of 6507

- 8K Addressable Bytes of Memory (A0-A12)
- On-the-chip Clock
- RDY Signal
- 8 Bit Bidirectional Data Bus

VSS	Н	1	40	
RDY	Н	2		φ ₂ (ουτ)
Φ1		3	38	s .o.
IRO		4		$\square \phi_2$
VSS RDY ϕ_1 IRQ VSS NMI SYNC VCC A0 A1	d	5		DBE
NMI		6	35	D N.C.
SYNC		7	24	D /MA/
vcc		8	33	D0 D1 D2 D3 D4 D5 D6 D6 D7 A15 A14
AO		9	32	01
A1		10	31	D2
A2		11	30	03
A3		12	29	D4
A4		13	28	D5
A5		14	27	D6
A6		15	26	70
A7		16	25	A15
A8		17	24	A14
A9		8 9 10 11 12 13 14 15 16 17 18 19 20	23	A13
A10		19	22	A12
A11		20	21	
		And a star to see the sector we have	Concernant of the	,

6512-40 Pin Package

Features of 6512

- 65K Addressable Bytes of Memory (A0-A15)
- IRQ Interrupt
- NMI Interrupt
- RDY Signal
- 8 Bit Bidirectional Data Bus
- SYNC Signal
- Two phase clock input
- Data Bus Enable

Φ1 2 2 IRQ 3 2 IRQ 3 2 NMI 4 2 VCC 5 2 A0 6 2 A1 7 2 A2 8 2 A3 9 2 A4 10 11 A6 12 1 A7 13 1	R AES P ϕ_2 R/W 00 D0 00 D1 00 D2 00 D3 00 D0 00 D1 000 D2 000 D3 000 D4 000 D5 000 D6 070 A11 000 A9 000	6513—28 Pin Package Features of 6513 • 4K Addressable Bytes of Memory (A0-A11) • Two phase clock input • TRQ Interrupt • NMI Interrupt • 8 Bit Bidirectional Data Bus

vss		1	28	RES
φ,		2	27	5 02
IRO		3	26	B R/W
vcc		4	25	00
AO		5	24	01
A1		6	23	02
A2		7	22	03
A3		8	21	04
A4		9	20	05
A5		10	19	D6
A6		11	18	507
A7		12	17	A12
8	2	13	16	5A11
A9		14	15	5 A10

6514-28 Pin Package

Features of 6514

- 8K Addressable Bytes of Memory (A0-A12)
- Two phase clock input
- IRQ Interrupt
- 8 Bit Bidirectional Data Bus

	1	28 RES
ROY	2	27 0 02
φ1 🗖	3	26 R/W
	4	25 00
vcc 🗖	5	24 01
A0 🗖	6	23 02
A1 🗖	7	22 03
A2 🗖	8	21 04
A3 🗖	9	20 05
A4 C	10	19 06
A5 🗖	11	18 07
A6 C	12	17 A11
A7 C	13	16 410
A8 C	14	15 49

6515-28 Pin Package

Features of 6515

- 4K Addressable Bytes of Memory (A0-A11)
- Two phase clock input
- IRQ Interrupt
- RDY Signal
- 8 Bit Bidirectional Data Bus

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